

Docket No.: GR 98 P 1801 C

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By: [Signature]

Date: May 14, 2003



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Kai Wurster et al.  
Applic. No. : 09/363,277  
Filed : July 28, 1999  
Title : Trench Capacitor with an Insulation Collar and Method for Producing a Trench Capacitor  
Examiner : Jennifer M. Kennedy - Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT  
UNDER 37 C.F.R. 1.97(C)(2)

Hon. Commissioner for Patents

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

United States Patent No. 5,670,805 (Hammerl et al.), dated September 23, 1997;

Korean Office Action dated November 28, 2002.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

05/19/2003 DTESSEM1 00000074 09363277

01 JUN 2006

180.00 DP

In accordance with 37 C.F.R. 1.97 (c) (2), consideration of this Information Disclosure Statement is requested.

Enclosed is the fee in the amount of \$180.00.

Respectfully submitted,

  
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For Applicants

Mark P. Weichselbaum  
Reg. No. 43,248

Date: May 14, 2003

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FORM PTO-1449 (SUBSTITUTE)

Attorney Docket No.:

Applic. No.

GR 98 P 1801 C

09/363,277

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

Applicant

Kai Wurster et al.

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT  
(37 CFR 1.98(b))Filing Date  
July 28, 1999Group Art Unit  
2812

## U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	5,670,805	09/23/97	Hammerl et al.			
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

## FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
	J						
	K						
	L						
	M						
	N						

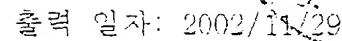
## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

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	P	

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



제3 부칙 5670805호 ('97. 10. 23) 제...

출력 일자: 2002/11/29

2002.11.28

특허청

심사4국

반도체2 심사담당관실

심사관 조지은



<<안내>>

문의사항이 있으시면 ☎ 042-481-5753 로 문의하시기 바랍니다.

특허청 직원 모두는 깨끗한 특허행정의 구현을 위하여 최선을 다하고 있습니다. 만일 업무처리과정에서 직원의 부조리행위가 있으면 신고하여 주시기 바랍니다.

▶ 홈페이지([www.kipo.go.kr](http://www.kipo.go.kr))내 부조리신고센터

### Notice to File a Response

Applicant's Name: Siemens AG

Attorney's Name: Sang-sun NAM

Patent Appln. No.: 10-1999-0022207

Title of Invention: A trench capacitor with isolation collar and  
corresponding manufacturing method

We hereby inform you of the following reason(s) for rejection pursuant to Article 63 of the Korean Patent Act. The applicant, if needed, may file an argument and an amendment no later than **January 28, 2003**.

#### R E A S O N (S)

Since the invention described in claims 1 and 16 of the present application could have been easily conceived by a person having ordinary skill in the art to which the present invention pertains from the document indicated below, which was published prior to the filing of the present application, this patent application cannot be patented according to Article 29(2) of the Korean Patent Act.

#### DETAILED GROUNDS

The present invention relates to a trench capacitor having insulation collar and its manufacturing method. The present invention is characterized by forming a buried contact and a conductive buried bridge on a substrate where the trench capacitor is formed. However, such a technical feature can be easily conceived by a person skilled in the art from USP No. 5,187,550 and USP No. 5,629,226 which disclose a P+ doping region adjacent to a source-drain region, and a n-type impurity diffusion region adjacent to a source-drain region formed along a trench side wall and a polysilicon region adjacent to said n-type impurities diffusion region electrically; and from USP No. 5,670,805 which discloses a trench capacitor having a constitution that a buried strap is electrically connected to a contacted side of the capacitor and a source-drain of a transfer gate.

[Attachment]

Attached 1: U.S. Patent No. 5,629,226 (March 13, 1997)

Attached 2: U.S. patent No. 5,187,550 (February 16, 1993)

Attached 3: U.S. patent No. 5,670,805 (October 23, 1997)

Date: November 28, 2002

Examiner: J. E. CHO

Examination Bureau IV

Korean Intellectual Property Office